

3-Pin Microprocessor Reset with Time-out and Voltage Window

Features

- Voltage Window monitoring
- Clear microprocessor restart after power up
- Processor reset at power down
- \blacksquare Reset output guaranteed down to $V_{DD} = 1 \text{ V}$
- Low power consumption: typ. 3 μ A at $V_{DD} = 5 \text{ V}$
- - 40 to +85 °C temperature range
- On request extended temperature range, -40 to +125 °C
- On-chip oscillator
- No external components required
- Push-pull or Open drain output
- TO-92 package
- Pin compatible with MC 33164

Description

The V6330 is a CMOS device which monitors the supply voltage of any electronic system, and generates the appropriate Reset signal. The gap between the two thresholds defines the allowed voltage range. As long as V_{DD} stays inside this voltage window, the output stays inactive. If V_{DD} drops below V_{THlow} , or rises above V_{THhigh} , the output gets active. When V_{DD} enters into the allowed range, the output remains active for an additional 50 ms (typ.). This allows the system to stabilize before getting fully active. The lower threshold voltage may be obtained in different versions:

2.0 V to 6 V

2.4 V to 6 V

2.8 V to 6 V

3.5 V to 6 V

4.0 V to 6 V

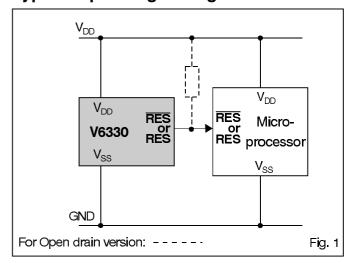
4.5 V to 6 V

Applications

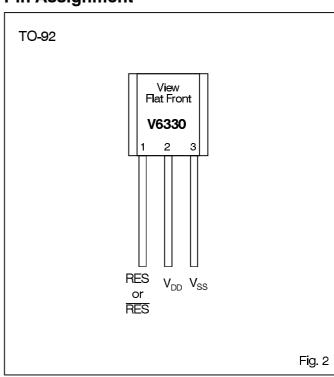
All microprocessor applications where an automatic restart is required:

- Computer electronics
- White / Brown goods
- Automotive electronics
- Industrial electronics
- Telecom systems
- Hand-held systems

Typical Operating Configuration



Pin Assignment





Absolute Maximum Ratings

Parameter	Symbol	Conditions
Voltage at V _{DD} to V _{SS}	V_{DD}	-0.3V to+10 V
Min. voltage at RES or RES	V_{min}	V _{SS} - 0.3 V
Max. voltage at RES or RES	V_{max}	V _{DD} + 0.3 V
Storage temperature range	T _{STO}	-65° to +150 °C

Table 1

Stresses above these listed maximum ratings may cause permanent damage to the device. Exposure beyond specified operating conditions may affect device reliability or cause malfunction.

Handling Procedures

This device has built-in protection against high static voltages or electric fields; however, anti-static precautions must be taken as for any other CMOS component. Unless otherwise specified, proper operation can only occur when all terminal voltages are kept within the supply voltage range.

Operating Conditions

Parameter	Symbol	Min.	Тур.	Max.	Units
Operating temperature ¹⁾	T _A	-40		+125	Ô
Positive supply voltage	V_{DD}	1		8	V

Table 2

Electrical Characteristics

 $T_A = -40$ to +85 °C, unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Min. at 25 °C	Тур.	Max. at 25 °C	Max.	Units
Supply current 1)	I _{DD}	$V_{DD} = 2 V$			1.5	2.1	3.1	μΑ
	I _{DD}	$V_{DD} = 5 V$			3.0	3.9	5.7	μΑ
	I _{DD}	$V_{DD} = 8 V$			5.2	6.8	10.0	μΑ
Threshold Low Voltage	$V_{TH low}$	Version: A,G,M	1.77	1.84	1.95	2.04	2.17	V
	$V_{TH low}$	Version: B,H,N	2.09	2.18	2.32	2.41	2.55	V
	$V_{TH\ low}$	Version: C,I,O	2.48	2.59	2.73	2.86	3.03	V
	V_{THlow}	Version: D,J,P	3.11	3.23	3.42	3.59	3.80	V
	$V_{TH\ low}$	Version: E,K,Q	3.55	3.70	3.88	4.08	4.32	V
	V_{THlow}	Version: F,L,R	4.05	4.22	4.42	4.67	4.95	V
Threshold High Voltage	$V_{TH\;high}$		5.58	5.79	6.10	6.42	6.82	V
Threshold hysteresis	V _{HYS}				25			mV
RES Output Low Level	V_{OL}	$V_{DD} = 5 \text{ V}, I_{OL} = 8 \text{ mA}$			175		400	mV
	V _{OL}	$V_{DD} = 3 \text{ V, } I_{OL} = 4 \text{ mA}$			140		300	mV
	V _{OL}	$V_{DD} = 1 \text{ V, } I_{OL} = 50 \mu\text{A}$			20		90	mV
RES Output High Level	V _{OH}	$V_{DD} = 5 \text{ V}, I_{OH} = -8 \text{ mA}$	4.3		4.5			V
	V _{OH}	$V_{DD} = 3 \text{ V}, I_{OH} = -4 \text{ mA}$	2.3		2.6			V
	V _{OH}	$V_{DD} = 1 \text{ V, } I_{OH} = -100 \mu\text{A}$	850		950			mV
Output leakage current 2)	I _{LEAK}	$V_{DD} = 5.5 \text{ V}$			0.05		1	μΑ

¹⁾ RES or RES open

Timing Characteristics

 $V_{DD} = 5.0 \text{ V}, T_{A} = -40 \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise specified}$

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Units
Power on reset time	t _{POR}		25	50	75	ms
Sensitivity around V _{THhigh 33}	t _{SEN high}	for $V_{DD} = 5 \text{ V to } 7 \text{ V in } 5 \mu\text{s}$	18	0.8 t _{Rhigh}		μS
L Sensitivity around $V_{\pi_{1},}$	t _{SEN low}	for $V_{DD} = 5 \text{ V to } 3 \text{ V in } 5 \mu\text{s}$	20	0.8 t _{Blow}		μS
Reaction time around V _{THhigh}	t _{Rhiah}	for $V_{DD} = 5 V$ to $7 V$ in 5μ s	20	55	90	μs
Reaction time around V _{THow} 3)	t _{B low}	for $V_{DD} = 5 \text{ V to } 3 \text{ V in } 5 \mu\text{s}$	22	75	150	μs

 $^{^{3)}}$ Tested on versions with V_{THIOW} higher than 3 V

Table 4

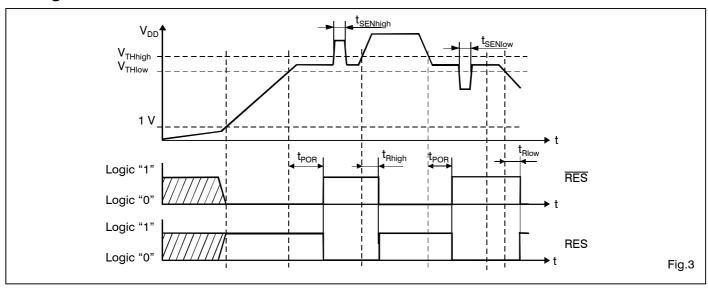
Table 3

¹⁾ The maximum operating temperature is confirmed by sampling at initial device qualification.

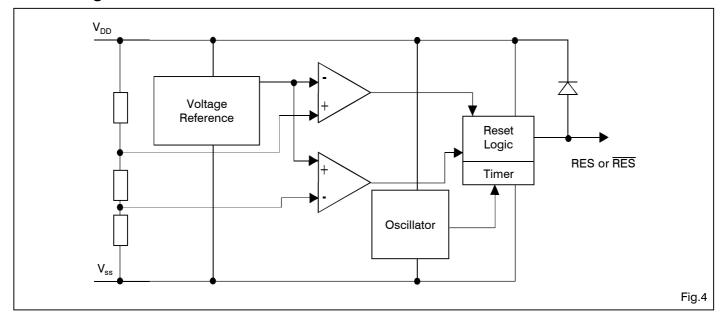
²⁾ Only for Open drain versions



Timing Waveforms



Block Diagram



Pin Description

TO-92

Pin	Name	Function
1	RES or RES	Reset output
2	V_{DD}	Pos itiv e Supply
3	V _{SS}	Supply ground

Table 5





Ordering Information

The V6330 is available with Push-pull or Open output stage and Reset active low or high.

Ordering form: V6330 < version letter> < packaging>

Example: Smart reset with: - Reset active low

- Open drain output

- 3.5 V threshold

- TO-92 package

V6330 P TO-92

When ordering, please specify the complete part number.

Version letter definition

Output stage	Threshold Low Voltage [V]					
	2.0	2.4	2.8	3.5	4.0	4.5
Push-pull, Reset active low Push-pull, Reset active high Open drain, Reset active low		B ¹⁾ H ¹⁾ N ¹⁾	C ¹⁾ I ¹⁾ O ¹⁾	D ¹⁾ J ¹⁾ P	E K ¹⁾ Q ¹⁾	F L ¹⁾ R ¹⁾

Table 6

Chip form on request

¹⁾ Non-stock items, minimum order 30 K pieces.